

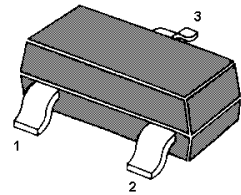
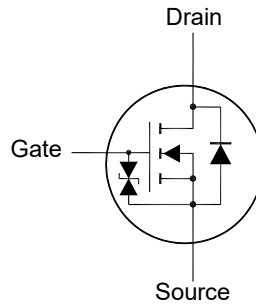
MMFTN506K

N-Channel Enhancement Mode MOSFET

Features

- Surface-mounted package
- Built-in G-S Protection Diode
- Typical ESD Protection HBM Class 1C

Classification	Voltage Range(V)
0A	< 125
0B	125 to < 250
1A	250 to < 500
1B	500 to < 1000
1C	1000 to < 2000
2	2000 to < 4000
3A	4000 to < 8000
3B	≥ 8000



1. Gate 2. Source 3. Drain
SOT-23 Plastic Package

Applications

- Portable appliances
- Battery management

Absolute Maximum Ratings (at $T_a = 25^\circ\text{C}$ unless otherwise specified)

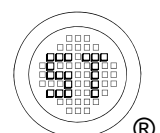
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	50	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	I_D	300	mA
Peak Drain Current, Pulsed ¹⁾	I_{DM}	800	mA
Total Power Dissipation ²⁾	P_{tot}	350	mW
Operating Junction and Storage Temperature Range	T_j, T_{stg}	- 55 to + 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance from Junction to Ambient ²⁾	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$

¹⁾ Pulse Test: Pulse Width $\leq 100 \mu\text{s}$, Duty Cycle $\leq 2\%$, Repetitive rating, pulse width limited by junction temperature $T_{j(\text{MAX})} = 150^\circ\text{C}$.

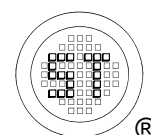
²⁾ Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad.



MMFTN506K

Characteristics at $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit
STATIC PARAMETERS					
Drain-Source Breakdown Voltage at $I_D = 10 \mu\text{A}$	BV_{DSS}	50	-	-	V
Drain-Source Leakage Current at $V_{DS} = 50 \text{ V}$	I_{DSS}	-	-	60	nA
Gate Leakage Current at $V_{GS} = \pm 12 \text{ V}$ at $V_{GS} = \pm 10 \text{ V}$ at $V_{GS} = \pm 5 \text{ V}$	I_{GSS}	- - -	- - -	± 1 ± 500 ± 50	μA nA nA
Gate-Source Threshold Voltage at $V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	$V_{GS(th)}$	0.49	-	1	V
Drain-Source On-State Resistance at $V_{GS} = 5 \text{ V}$, $I_D = 50 \text{ mA}$ at $V_{GS} = 2.5 \text{ V}$, $I_D = 50 \text{ mA}$ at $V_{GS} = 1.8 \text{ V}$, $I_D = 50 \text{ mA}$	$R_{DS(on)}$	- - -	- - -	2 2.5 4	Ω
DYNAMIC PARAMETERS					
Forward Transconductance at $V_{DS} = 10 \text{ V}$, $I_D = 0.2 \text{ A}$	g_{fs}	-	0.71	-	S
Input Capacitance at $V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$	C_{iss}	-	32	-	pF
Output Capacitance at $V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$	C_{oss}	-	10.2	-	pF
Reverse Transfer Capacitance at $V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$	C_{rss}	-	7.5	-	pF
Gate charge total at $V_{DS} = 25 \text{ V}$, $I_D = 0.8 \text{ A}$, $V_{GS} = 10 \text{ V}$ at $V_{DS} = 25 \text{ V}$, $I_D = 0.8 \text{ A}$, $V_{GS} = 4.5 \text{ V}$	Q_g	- -	1.3 0.85	- -	nC
Gate to Source Charge at $V_{DS} = 25 \text{ V}$, $I_D = 0.8 \text{ A}$, $V_{GS} = 10 \text{ V}$	Q_{gs}	-	0.45	-	nC
Gate to Drain Charge at $V_{DS} = 25 \text{ V}$, $I_D = 0.8 \text{ A}$, $V_{GS} = 10 \text{ V}$	Q_{gd}	-	0.3	-	nC
Turn-On Delay Time at $V_{GS} = 10 \text{ V}$, $V_{DS} = 30 \text{ V}$, $R_G = 25 \Omega$, $I_D = 0.5 \text{ A}$	$t_{d(on)}$	-	5.4	-	ns
Turn-On Rise Time at $V_{GS} = 10 \text{ V}$, $V_{DS} = 30 \text{ V}$, $R_G = 25 \Omega$, $I_D = 0.5 \text{ A}$	t_r	-	2.7	-	ns
Turn-Off Delay Time at $V_{GS} = 10 \text{ V}$, $V_{DS} = 30 \text{ V}$, $R_G = 25 \Omega$, $I_D = 0.5 \text{ A}$	$t_{d(off)}$	-	5.8	-	ns
Turn-Off Fall Time at $V_{GS} = 10 \text{ V}$, $V_{DS} = 30 \text{ V}$, $R_G = 25 \Omega$, $I_D = 0.5 \text{ A}$	t_f	-	30	-	ns
Body-Diode PARAMETERS					
Drain-Source Diode Forward Voltage at $I_S = 115 \text{ mA}$	V_{SD}	0.5	-	1.4	V
Body-Diode Continuous Current	I_S	-	-	300	mA



Electrical Characteristics Curves

Fig. 1 Typical Output Characteristics

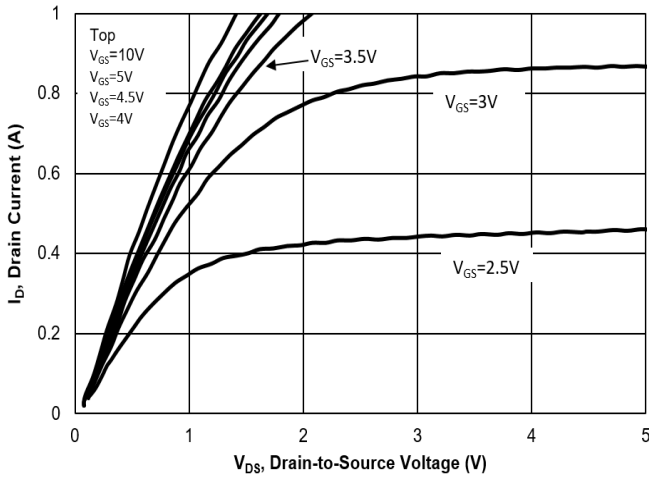


Fig. 2 Typical Transfer Characteristics

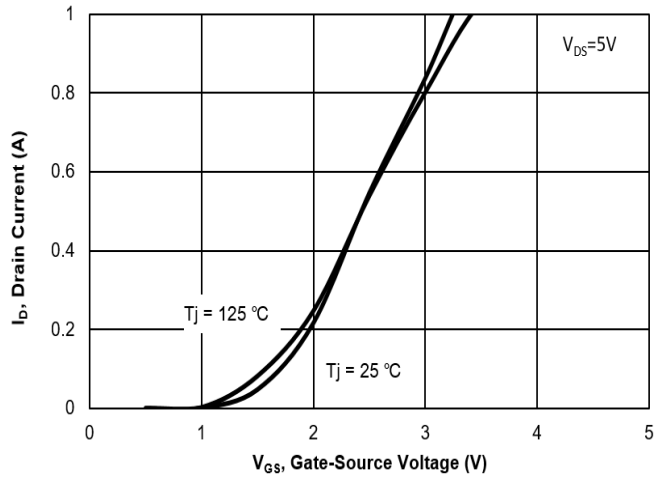


Fig. 3 On-Resistance vs. Drain Current

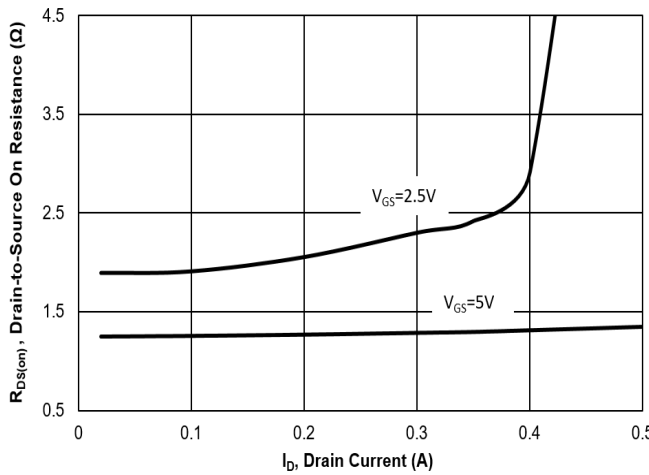


Fig. 4 On-Resistance vs. Gate-Source Voltage

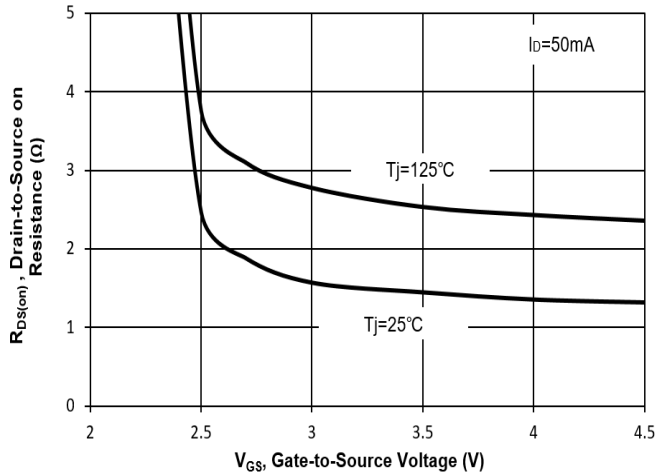


Fig. 5 On-Resistance vs. T_j

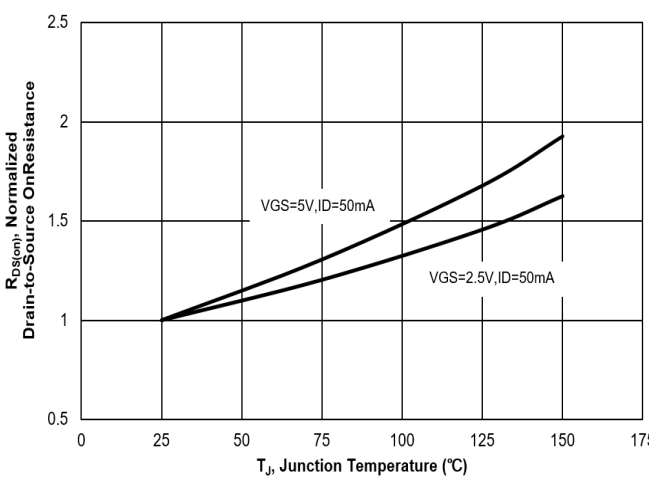
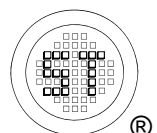
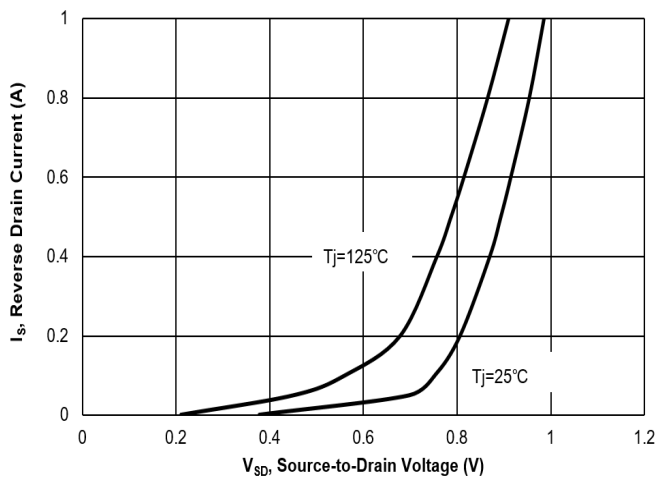


Fig. 6 Typical Body-Diode Forward Characteristics



Electrical Characteristics Curves

Fig. 7 Typical Junction Capacitance

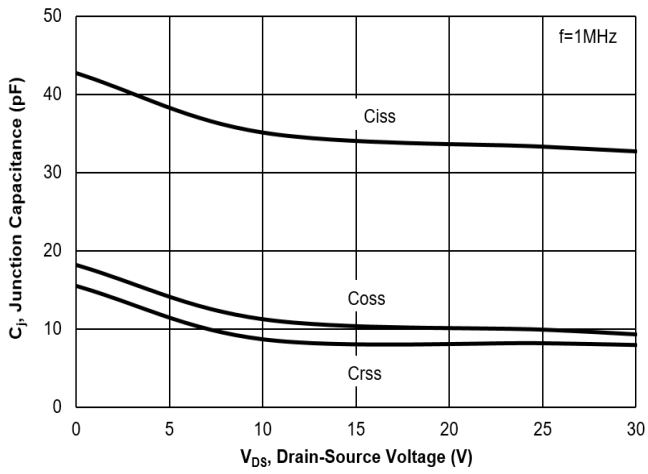


Fig. 8 Gate Charge

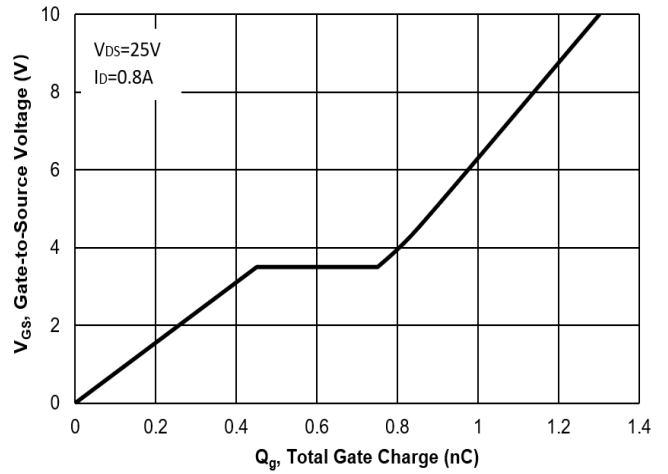


Fig. 9 $V_{(BR)DSS}$ vs. Junction Temperature

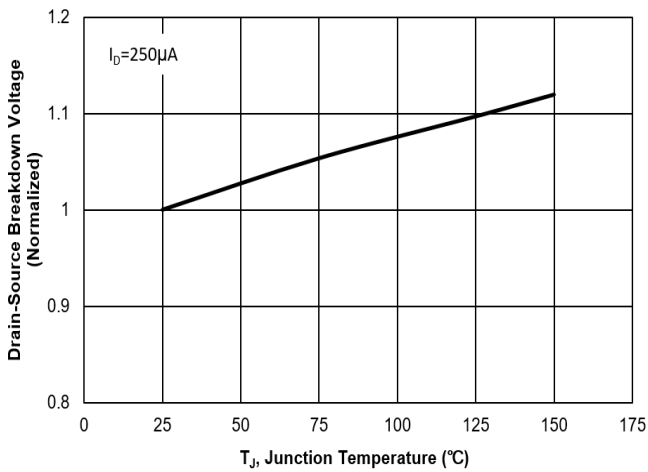
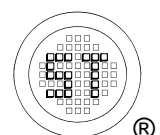
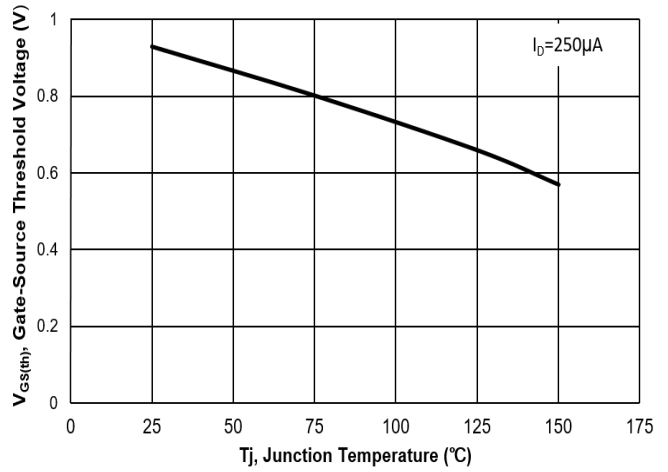


Fig. 10 Gate Threshold Variation vs. T_j



Test Circuits

Fig.1-1 Switching times test circuit

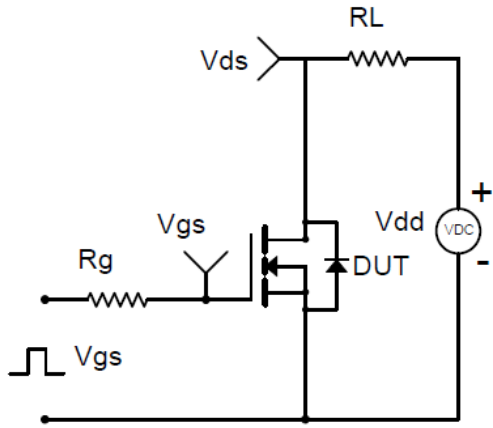


Fig.1-2 Switching Waveform

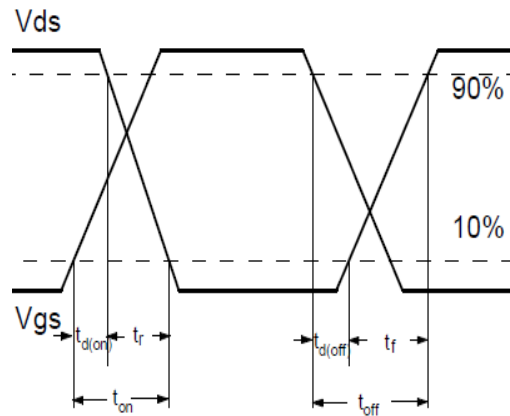


Fig.2-1 Gate charge test circuit

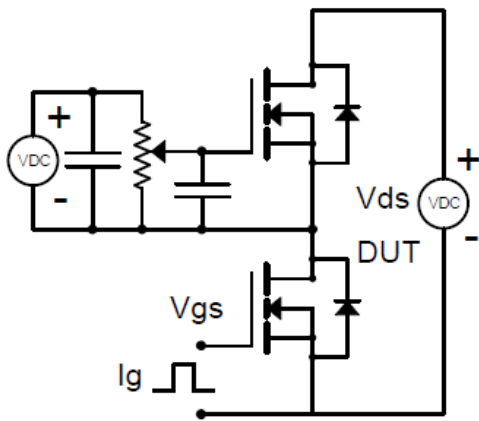
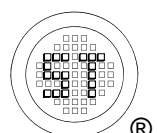
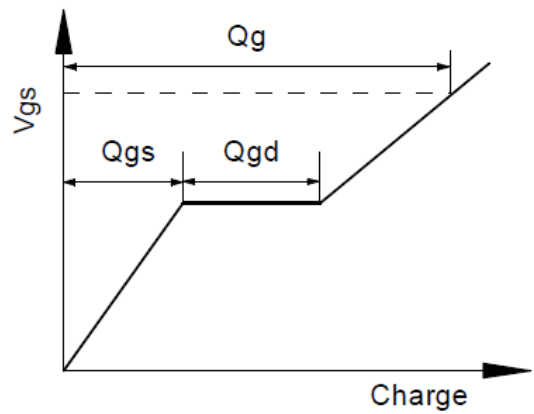


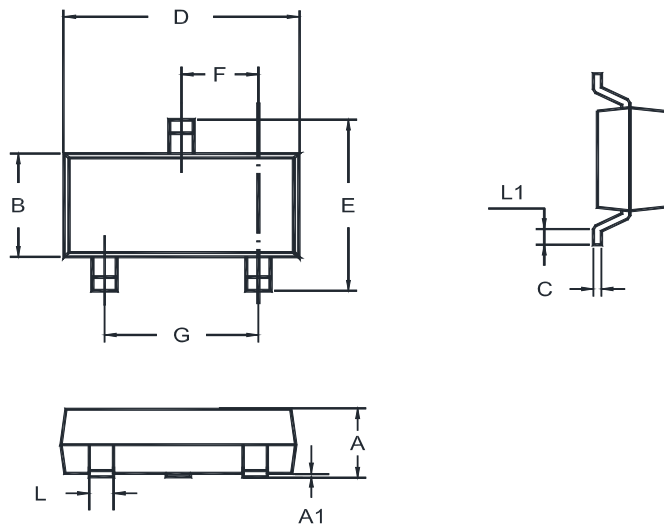
Fig.2-2 Gate charge waveform



MMFTN506K

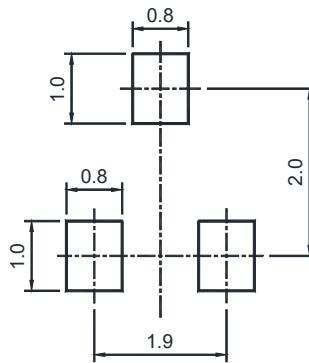
Package Outline (Dimensions in mm)

SOT-23



Unit	A	A1	B	C	D	E	F	G	L	L1
mm	1.20	0.100	1.40	0.19	3.04	2.6	1.02	2.04	0.51	0.2
	0.89	0.013	1.20	0.08	2.80	2.2	0.89	1.78	0.37	MIN

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
SOT-23	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

Marking information

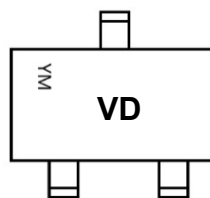
" VD " = Part No.

" YM " = Date Code Marking

" Y " = Year

" M " = Month

Font type: Arial



Disclaimer: Our company reserve the right to make modifications, enhancements, improvements, corrections or other changes to improve product design, functions and reliability, anytime without notice. Semtech Electronics Limited makes no warranties, representations or warranties regarding the suitability of its products for any particular purpose, and does not accept any liability arising from the application or use of any product or circuit such as: Apply to medical, military, aircraft, space or life support equipment and expressly waive any and all liability, including but not limited to special, consequential or collateral damage.

